TOSHIBA

TOSHIBA Original CMOS 4-Bit Microcontroller

TLCS-47 Series

TMP47P206VMG TMP47P206VPG

TOSHIBA CORPORATION

Semiconductor Company

Document Change Notification

The purpose of this notification is to inform customers about the launch of the Pb-free version of the device. The introduction of a Pb-free replacement affects the datasheet. Please understand that this notification is intended as a temporary substitute for a revision of the datasheet.

Changes to the datasheet may include the following, though not all of them may apply to this particular device.

1. Part number

Example: TMPxxxxxF TMPxxxxxFG

All references to the previous part number were left unchanged in body text. The new part number is indicated on the prelims pages (cover page and this notification).

2. Package code and package dimensions

Example: LQFP100-P-1414-0.50C LQFP100-P-1414-0.50F

All references to the previous package code and package dimensions were left unchanged in body text. The new ones are indicated on the prelims pages.

3. Addition of notes on lead solderability

Now that the device is Pb-free, notes on lead solderability have been added.

4. RESTRICTIONS ON PRODUCT USE

The previous (obsolete) provision might be left unchanged on page 1 of body text. A new replacement is included on the next page.

5. Publication date of the datasheet

The publication date at the lower right corner of the prelims pages applies to the new device.

1. Part number

2. Package code and dimensions

Previous Part Number (in Body Text)	Previous Package Code (in Body Text)	New Part Number	New Package Code	OTP
TMP47P206VP	P-DIP20-300-2.54A	TMP47P206VPG	DIP20-P-300-2.54A	—
TMP47P206VM	P-SOP20-300-1.27	TMP47P206VMG	SOP20-P-300-1.27	—

*: For the dimensions of the new package, see the attached Package Dimensions diagram.

3. Addition of notes on lead solderability

The following solderability test is conducted on the new device.

Lead solderability of Pb-free devices (with the G suffix)

Test	Test Conditions	Remark
Solderability	 (1) Use of Lead (Pb) solder bath temperature = 230°C dipping time = 5 seconds the number of times = once use of R-type flux (2) Use of Lead (Pb)-Free solder bath temperature = 245°C dipping time = 5 seconds the number of times = once use of R-type flux 	Leads with over 95% solder coverage till lead forming are acceptable.

4. RESTRICTIONS ON PRODUCT USE

The following replaces the "RESTRICTIONS ON PRODUCT USE" on page 1 of body text.

RESTRICTIONS ON PRODUCT USE

• The information contained herein is subject to change without notice.

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- For a discussion of how the reliability of microcontrollers can be predicted, please refer to Section 1.3 of the chapter entitled Quality and Reliability Assurance/Handling Precautions.

5. Publication date of the datasheet

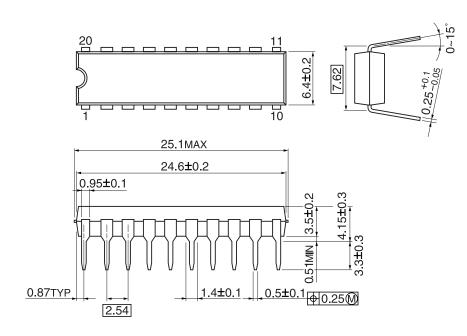
The publication date of this datasheet is printed at the lower right corner of this notification.

(Annex)

Package Dimensions

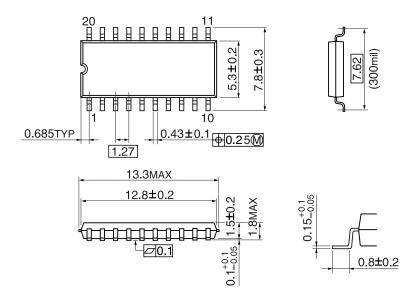
DIP20-P-300-2.54A

Unit: mm



SOP20-P-300-1.27

Unit: mm



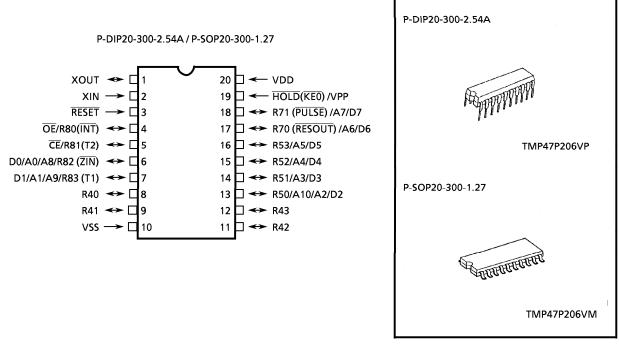
CMOS 4-Bit Microcontroller

TMP47P206VM/P

The TMP47P206V is the OTP microcontroller with 16 Kbit PROM. For program operation, the programming is achieved by using with EPROM programmer (TC57256AD type) and adapter socket. The function of this device is exactly same as the TMP47C206.

Part No.	ROM	RAM	Package	OTP
TMP47P206VP	OTP	100 · · 4 hit	P-DIP20-300-2.54A	BM11125
TMP47P206VM	2048 × 8-bit	128 x 4-bit	P-SOP20-300-1.27	BM11126

Pin Assignment (Top View)



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 The products described in this document are subject to the foreign exchange and foreign trade laws.
 The information contained herein is presented only as a guide for the applica

Pin Function

The TMP47P206V has MCU mode and PROM mode.

(1) MCU mode

The TMP47C206 and the TMP47P206V are pin compatible.

(2) PROM mode

Pin Name	Input / Output	Functions	Pin Name (MCU mode)				
D0/A0/A8			R82				
D1/A1/A9			R83				
D2/A2/A10]		R50				
D3/A3]		R51				
D4 / A4	I/O	Data inputs / outputs or Address inputs	R52				
D5/A5			R53				
D6/A6			R70				
D7/A7			R71				
ŌĒ	Incut	Output Enable input	R80				
CE	Input	Chip Enable input	R81				
VPP		+ 12.5 V / 5 V (Program supply voltage)	HOLD				
VCC	Power supply	+ 5 V	VDD				
VSS		0 V	VSS				
R43 to R40	I/O	Be fixed to low level.					
RESET	Input	Be fixed to non connection.					
XIN	Input	Input the clock from the external oscillator.					
XOUT	Input	PROM control input					

Operational Description

The following is an explanation of hardware configuration and operation in relation to the TMP47P206V. The TMP47P206V is the same as the TMP47C206 except that an OTP is used instead of a built-in mask ROM.

1. Operation mode

The TMP47P206V has a MCU mode and a PROM mode.

1.1 MCU mode

The MCU mode is set by attaching a resonator between the XIN and XOUT pins. Operation in the MCU mode is the same as for the TMP47C206. In the TMP47P206V, RC oscillation is impossible.

1.1.1 Program Memory

The program storage area is the same as for the TMP47C206.

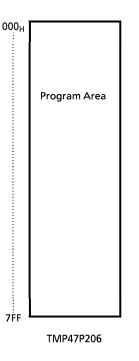


Figure 1-1. Program Area

1.1.2 Data Memory

The TMP47P206V has 128 × 4-bit of data memory (RAM).

1.1.3 Input / Output Circuitry

(1) Control pins

This is the same as I/O code FB of the TMP47C206. In the TMP47P206V, RC oscillator is impossible. Connecting the resonator is required when using as evaluator of I/O code FE.

(2) I/O Ports

The input / output circuit of the TMP47P206V is the same as the TMP47C206.

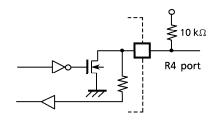


Figure 1-2. I/O code and external circuitry

1.2 PROM mode

The TMP47P206V enters PROM mode by sending external clock signal from XIN pin when XOUT pin is at low level. In PROM mode, programs can be written or verified using a general-purpose PROM writer with an adapter socket being attached.

With the TMP47P206V, the PROM address input and data input/output use the same port. PROM mode control signal (XOUT) is used for switching between two functions. XOUT pin becomes control signal input after PROM mode is completed.

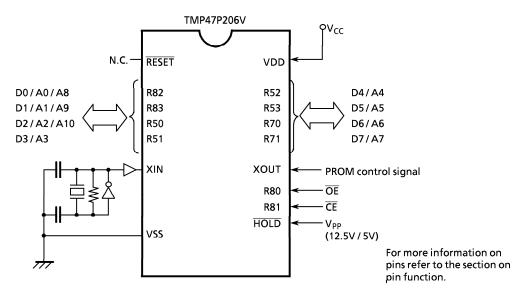


Figure 1-3. Setting for PROM mode

1.2.1 Program Writing

When writing a program, set a ROM type to "TC57256AD" (programming voltage: 12.5 V). Since the TMP47P206V has a 2048 \times 8-bit internal PROM (000 to 7FF_H), set a stop address of a PROM writer to "7FF_H". Please use a general-purpose PROM writer which does not have an electric signature mode or can release from it.

1.2.2 High Speed Programming Mode

The program time can be greatly decreased by using this high speed programming mode. The device is set up in the high speed programming mode when the programming voltage (+ 12.5 V) is applied to the V_{PP} terminal with V_{CC} = 6 V and $\overline{CE} = V_{IH}$.

The programming is achieved by applying a single low level 1ms pulse the CE input after addresses and data are stable. Then the programmed data is verified by using Program Verify Mode.

If the programmed data is not correct, another program pulse of 1ms is applied and then programmed data is verified. This should be repeated until the program operates correctly (max. 25 times).

After correctly programming the selected address, one additional program pulse with pulse width 3 times that needed for programming is applied.

When programming has been completed, the data in all addresses should be verified with $V_{CC} = V_{PP} = 5 V$.

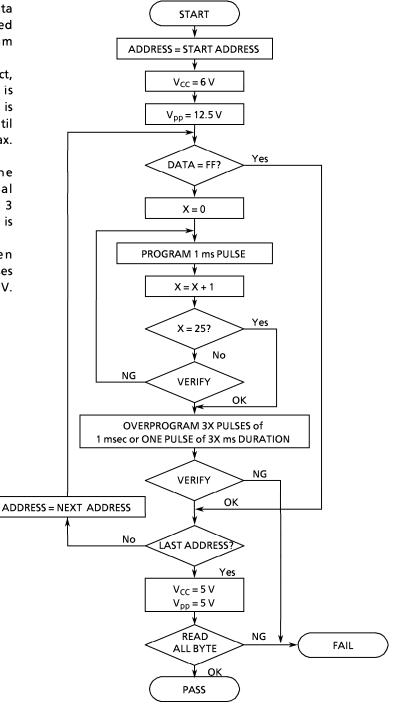


Figure 1-4. Flowchart

Electrical Characteristics

Absolute Maximum Ratings	(V _{SS} =
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Parameter	Symbol	Pins	Ratings	Unit	
Supply Voltage	V _{DD}		– 0.3 to 6.5	V	
Program Voltage	V _{PP}	HOLD / V _{PP}	– 0.3 to 13.0	V	
Input Voltage	V _{IN}		- 0.3 to V _{DD} + 0.3	V	
Output Voltage	V _{OUT}		- 0.3 to V _{DD} + 0.3	V	
Output Consert (Der 1 sis)	I _{OUT1}	Port R4, R50	30		
Output Current (Per 1 pin)	I _{OUT2}	Port R51 to 53, R8, R70, R71	3.2	mA	
Output Current (Total)	ΣI_{OUT1}	Port R4, R50	100		
Output Current (Total)	ΣI_{OUT2}	Port R51 to 53, R8, R70, R71	28.8	mA	
		SOP	150		
Power Dissipation [Topr = 85°C]	PD	DIP	250	- mW	
Soldering Temperature (time)	Tsld		260 (10 s)	°C	
Storage Temperature	Tstg		– 55 to 125	°C	
Operating Temperature	Topr		– 40 to 85	°C	

0 V)

Note: The absolute maximum ratings are rated values which must not be exceeded during operation, even for an instant. Any one of the ratings must not be exceeded. If any absolute maximum rating is exceeded, a device may break down or its performance may be degraded, causing it to catch fire or explode resulting in injury to the user. Thus, when designing products which include this device, ensure that no absolute maximum rating value will ever be exceeded.

Recommended Operating Conditions	$(V_{SS} = 0 V, Topr = -40 to 85^{\circ}C)$
Incommended operating conditions	$(v_{33} = 0, v_{10}) = +0.000 C/$

Parameter	Symbol		Pins	Conditions		Min	Max	Unit
			Newsel	Crystar	fc = 8 MHz	4.0 (2.7) * ²		
Supply \alto go	N		Normal	or ceramic	fc = 4.2 MHz	4.0 (2.2) *2	5.7	
Supply Voltage	V _{DD}		mode	RC	fc = 2.5 MHz	4.0 (2.2) * ²	5./	V V
			HOLD mode	-	-	4.0 (2.0) * ²		
	V _{IH1}	Except Hysteresis Input		In the	normal	$V_{DD} \times 0.7$		
Input High Voltage	V _{IH2}	Hysteresis Input		operating area		$V_{DD} \times 0.75$	V _{DD}	V
	V _{IH3}			In the HOLD mode		V _{DD} ×0.9		
	V _{IL1}	Except Hysteresis Input		In the normal			V _{DD} × 0.3	
Input Low Voltage	V _{IL2}	Hysteresi	Hysteresis Input		operating area		V _{DD} × 0.25) v
	V _{IL3}				In the HOLD mode		V _{DD} × 0.1	
Clock Frequency	fc		T	$V_{DD} = 2$	V _{DD} = 2.7 to 5.7 V		8	MHz
		fc XIN, XOUT		$V_{DD} = 2$	$V_{DD} = 2.2 \text{ to } 5.7 \text{ V}$		4.2	WIHZ

Note 1: The recommended operating conditions for a device are operating conditions under which it can be guaranteed that the device will operate as specified. If the device is used under operating conditions other than the recommended operating conditions (supply voltage, operating temperature range, specified AC/DC values etc.), malfunction may occur. Thus, when designing products which include this device, ensure that the recommended operating conditions for the device are always adhered to.

Note 2: LVD id initially enable and initial Min. V_{DD} is 4.0 V. After LVD is disabled above 4.0 V. Min. V_{DD} will be 2.7 or 2.2 to 2.0 V.

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DC Characterist	ics	$(V_{SS} = 0 V, Topr = -40)$	to 85°C)					
Parameter	Symbol	Pins	Conditions	Min	Тур.	Max	Unit	
Hysteresis Voltage	V _{HS}	Hysteresis Input		-	0.7	_	v	
	I _{IN1} (Note 1)	RESET, HOLD						
Input Current	I _{IN2}	Open drain output ports	$\nabla_{DD} = 5.7 V, V_{IN} = 5.7 V / 0 V$	-	-	±2	μΑ	
Input Resistance	R _{IN}	RESET		100	220	450		
Pull down Resistance	R _{PD}	R82		22	70	160	kΩ	
Input Low Current	I _{IL}	Push-pull output ports	$V_{DD} = 5.7 \text{ V}, \ V_{IN} = 0.4 \text{ V}$	-	-	- 2	mA	
Output Leakage Current	I _{LO}	Open drain output ports	V _{DD} = 5.7 V, V _{OUT} = 5.7 V	-	-	2	μΑ	
			$V_{DD} = 5 V, I_{OH} = -100 \mu A$	4.8	-	-		
Output High Voltage	V _{OH}	Push-pull output ports	$V_{DD} = 4.5 \text{ V}, \ I_{OH} = -200 \ \mu\text{A}$	2.4	-	-	v [
			$V_{DD} = 2.2 \text{ V}, \ I_{OH} = -5 \ \mu \text{A}$	2.0	-	-		
			$V_{DD} = 4.5 V, I_{OL} = 3.3 mA$	-	_	1.0	- v	
	V _{OL1}	Port R8, R7, R51 to 53	$V_{DD} = 4.5 V, I_{OL} = 1.6 mA$	-	-	0.4		
Output Low			$V_{DD} = 2.2 \text{ V}, \ I_{OL} = 20 \ \mu \text{A}$	-	-	0.1		
Voltage			$V_{DD} = 4.5 V, I_{OL} = 15 mA$	-	-	1.0		
	V _{OL2}	Port R4, R50	$V_{DD} = 4.5 V, I_{OL} = 7 mA$	-	-	0.4		
			$V_{DD} = 2.2 \text{ V}, \ I_{OL} = 50 \ \mu\text{A}$	-	-	0.1		
	I _{OL1}	Port R8, R7, R51 to 53	$V_{DD} = 4.5 V, V_{OL} = 0.4 V$	1.6	-	-		
Output Low Current			$V_{DD} = 4.5 V, V_{OL} = 1.0 V$	15	-	-	mA	
	I _{OL2}	Port R4, R50	$V_{DD} = 4.5 V, V_{OL} = 0.4 V$	7	17	-		
			$V_{DD} = 5.7 V$, fc = 8 MHz	-	3	6		
Supply Current (in the Normal operating			$V_{DD} = 5.7 V$, fc = 4 MHz	-	2	4		
mode) (Note 2)	I _{DD}		$V_{DD} = 3.0 V$, fc = 4 MHz	-	1	2	mA	
			$V_{DD} = 3.0 V$, fc = 1 MHz	-	0.6	1.2		
Supply Current (in the HOLD operating		LVD always Enable	V _{DD} = 5.7 V	-	50	200		
node) (Note 2)	IDDH	LVD On and Off	V _{DD} = 5.7 V –		2.5	20	μA	
Injection Current	Izc	R82		-	_	1	mA	

< General Conditions>

Typ. values show those at Topr = 25° C, V_{DD} = 5 V.

Note 1: Input Current I_{IN1}: The current through resistor is not included.

Note 2: Supply Current: $V_{IN} = 5.5 \text{ V} / 0.2 \text{ V} (V_{DD} = 5.7 \text{ V}) \text{ or } 2.8 \text{ V} / 0.2 \text{ V} (V_{DD} = 3.0 \text{ V})$

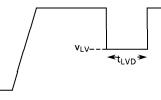
AC Characteristics	(√ _{SS} = 0 V, To	pr = - 40 to 85°C))			
Parameter	Symbol	Co	nditions	Min	Тур.	Max	Unit
			V_{DD} = 2.7 to 5.7 V	1.0		8	
Instruction Cycle Time	tcy		V _{DD} = 2.2 to 5.7 V	1.9	-		μs
			$V_{DD} \ge 2.7 V$	60		_	ns
High level Clock pulse Width	t _{WCH}	For external clock	V _{DD} <2.7 V	120			
		operation	$V_{DD} \ge 2.7 V$	60			
Low level Clock pulse Width	t _{WCL}		V _{DD} <2.7 V	120			
Delay Reset Output Signal	t _{rd}	fc = 1 MHz		_	_	16	μs

Low Voltage Detector Characteristics

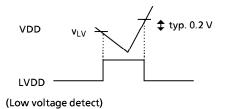
 $(V_{SS} = 0 V, Topr = -40 to 85^{\circ}C)$

Parameter		Symbol	Conditions	Min	Тур.	Max	Unit
LVD interval time	(Note 1)	t _{int}		8.5	-	128	ms
LVD Enable time	(Note 1)	t _{en}		100	-	-	μ S
LVD pulse width	(Note 1, 2)	t _{LVD}		50	-	-	μ S
Detection Voltage (N	(Note 3) V	V _{LV}	LVDDTY = 0 LVDD = 0	2.7	3.3	3.8	v
			LVDDTY = 1 LVDD = 0	2.2	2.7	3.3	
LVD Operating Voltage	(Note 1)	V _{LVD}		2.0	_	_	v

Note 1: These parameters are characterized but not tested. Note 2: Less than Min. t_{LVD} , CPU will not be reset.

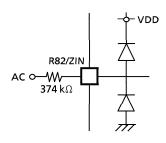


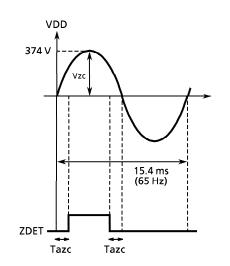
Note 3: Detection voltage has typ. 0.2 V hysteresis.



Zero-Cross Detection Ch	Zero-Cross Detection Characteristics				5°C)		
Parameter	Symbol		Conditions	Min	Тур.	Max	Unit
Zero-cross Accuracy	Tazc	fzc = 45 1	fzc = 45 to 65 Hz (*)			90	μ S
Injection Current	lzc					1	mA
Pull-down resistance	R _{PD}			22	70	160	kΩ

(*) Measurement conditions



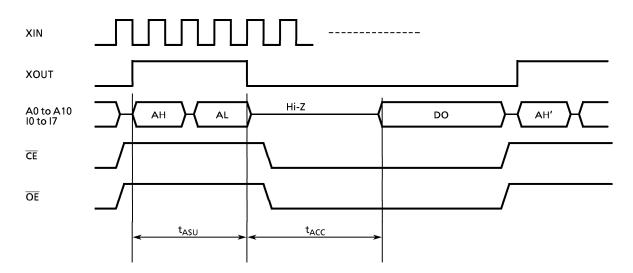


(1) 8 MHz				XIN	<u>хоц</u> т
Ceramic Resonate CSA8.00MGU	or (MURATA)	$C_{XIN} = C_{XOU}$	r = 30pF	L Ce	ramic
KBR-8.00MS	(KYOCERA)	$C_{XIN} = C_{XOU}$			rystal
EFOEC8004A4	(NATIONAL)		•	C _{XIN}	
(2) 6 MHz					
Ceramic Resonate	or				
CSA6.00MGU	(MURATA)	$C_{XIN} = C_{XOU}$	_F = 30pF		
KBR-6.00MS	(KYOCERA)	$C_{XIN} = C_{XOU}$	-		
EFOEC6004A4	(NATIONAL)	$C_{XIN} = C_{XOU}$	_r = 30pF		
(3) 4 MHz					
Ceramic Resonate	or				
CSA4.00MGU	(MURATA)	$C_{XIN} = C_{XOU}$	_r = 30pF		
KBR-4.00MS	(KYOCERA)	$C_{XIN} = C_{XOU}$	_r = 30pF		
EFOEC4004A4	(NATIONAL)	$C_{XIN} = C_{XOU}$	_r = 30pF		
Crystal Oscillator					
204B-6F 4.0000	(TOYOCOM)	$C_{XIN} = C_{XOU}$	_r = 20pF		
(4) 1 MHz					
Ceramic Resonato	r				
CSA1.00MGU	(MURATA)	$C_{XIN} = C_{XOU}$	_r = 30pF		
KBR-1.00MS	(KYOCERA)				
EFOEC1004A4	(NATIONAL)	~ ~	20.5		

DC/AC Characteristics (V_{SS} = 0 V)

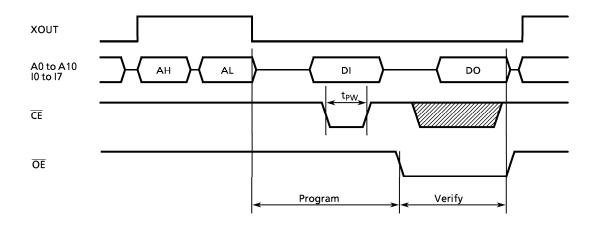
(1) Read Operation

Parameter	Symbol	Condition	Min	Тур.	Max	Unit
Output Level High Voltage	V _{IH4}		V _{CC} × 0.7	-	V _{CC}	v
Output Level Low Voltage	V _{IL4}		0	-	V _{CC} × 0.3	v
Supply Voltage	V _{CC}		4.75	-	6.0	v
Programming Voltage	V _{PP}					
Address Set-up Time	t _{ASU}		350	-	-	ns
Address Access Time	t _{ACC}	V _{CC} = 5.0 ± 0.25 V	-	-	300	ns



(2)	High Speed	Programming	Operation
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Parameter	Symbol	Condition	Min	Тур.	Max	Unit
Input High Voltage	V _{IH4}		V _{CC} × 0.7	-	V _{CC}	V
Input Low Voltage	V _{IL4}		0	-	V _{CC} × 0.3	v
Supply Voltage	V _{CC}		4.75	-	6.0	v
V _{PP} Power Supply Voltage	V _{PP}		12.25	12.50	12.75	v
Programming Pulse Width	t _{PW}	V _{CC} = 6.0 ± 0.25 V	0.095	0.1	0.105	ms



Note: DO; Data output (10 to 17), AL; Address input (A0 to A7) DI; Data input (10 to 17), AH; Address input (A8 to A10)